P2004,0226

Abstract

Method for the production of a bipolar transistor comprising an improved base terminal

For the production of an improved bipolar transistor comprising a low-resistance base terminal, it is proposed that a dielectric layer is deposited over the semiconductor substrate and is highly doped via an implantation mask. In a subsequent controlled thermal step, the dopant is then indiffused into the semiconductor substrate from the dielectric layer serving as a dopant repository. This gives rise to a low-resistance region with which the extrinsic base can be defined carefully.

Figure 6